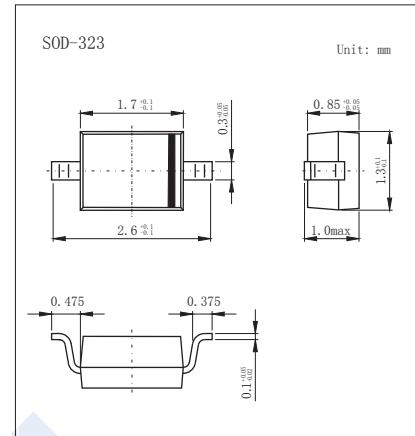


Schottky Diodes

BAT54HT1 (KAT54HT1)

■ Features

- Extremely Fast Switching Speed
- Low Forward Voltage
- Pb-Free Package is Available



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Reverse Voltage	V _{RM}	30	V
Forward Current	I _F	200	mA
Repetitive Peak Forward Current	I _{FRM}	300	
Non-Repetitive Peak Forward Current (t < 1s)	I _{FSM}	600	
Power Dissipation	P _d	200	mW
-Derate above 25°C		1.57	mW/°C
Thermal Resistance Junction to Ambient	R _{θ JA}	635	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _R	I _R = 10 uA	30			V
Forward voltage	V _F	I _F = 0.1 mA			0.24	
		I _F = 1 mA			0.32	
		I _F = 10 mA			0.4	
		I _F = 30 mA			0.5	
		I _F = 100 mA			0.8	
Reverse voltage leakage current	I _R	V _R = 25 V			2	uA
Junction capacitance	C _j	V _R = 1 V, f = 1 MHz			10	pF
Reverse recovery time	t _{rr}	I _F = I _R = 10 mA, I _{R(REC)} = 1 mA			5	ns

■ Marking

Marking	JV*
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Schottky Diodes

BAT54HT1 (KAT54HT1)

■ Typical Characteristics

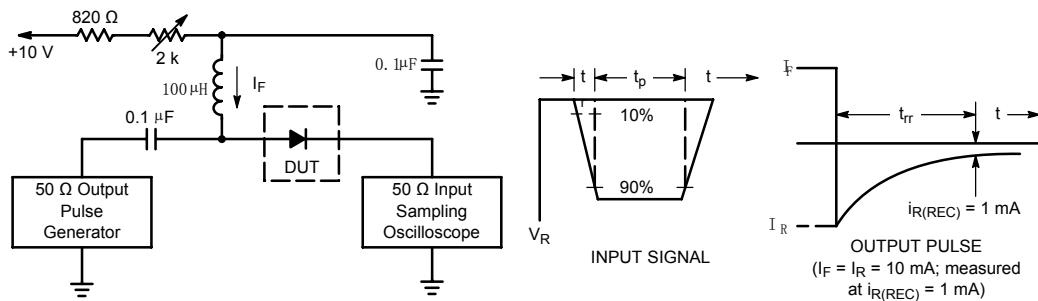


Figure 1. Recovery Time Equivalent Test Circuit

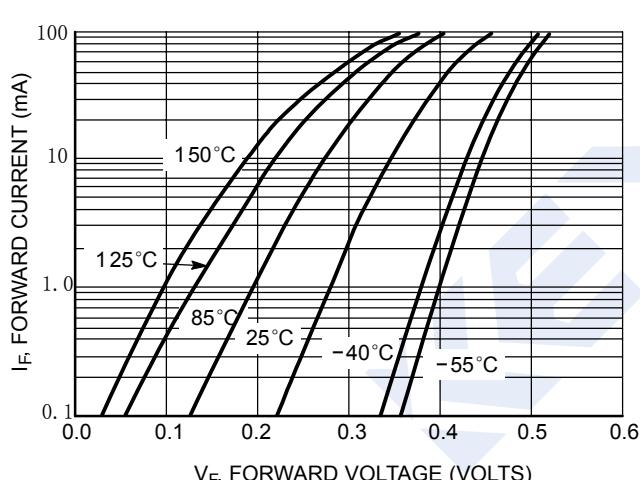


Figure 2. Forward Voltage

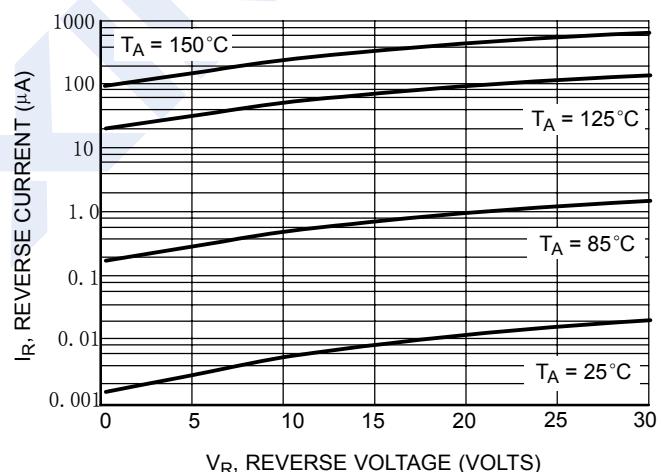


Figure 3. Leakage Current

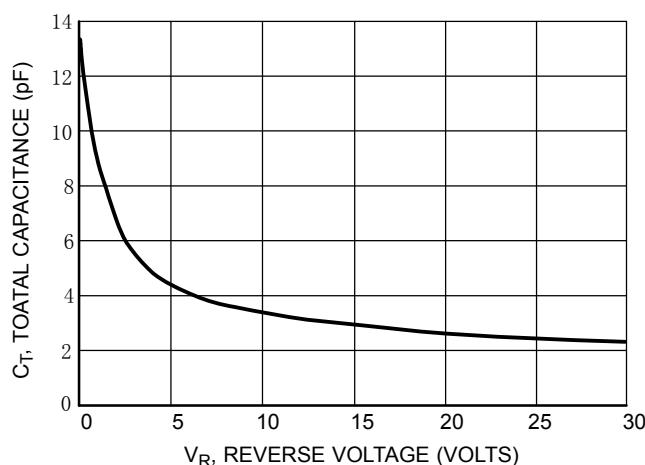


Figure 4. Total Capacitance